

# NPN - MJ15022, MJ15024\*

\*MJ15024 is a Preferred Device

## Silicon Power Transistors

The MJ15022 and MJ15024 are PowerBase power transistors designed for high power audio, disk head positioners and other linear applications.

### Features

- High Safe Operating Area (100% Tested) – 2 A @ 80 V
- High DC Current Gain –  $h_{FE} = 15$  (Min) @  $I_C = 8$  Adc
- Pb-Free Packages are Available\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MJ15022 MJ15024	$V_{CEO}$	200 250	Vdc
Collector-Base Voltage MJ15022 MJ15024	$V_{CBO}$	350 400	Vdc
Emitter-Base Voltage	$V_{EBO}$	5	Vdc
Collector-Emitter Voltage	$V_{CEX}$	400	Vdc
Collector Current – Continuous – Peak (Note 1)	$I_C$	16 30	Adc
Base Current – Continuous	$I_B$	5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	250 1.43	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.70	$^\circ\text{C}/\text{W}$

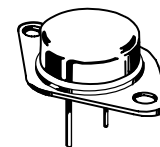
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq 10\%$ .



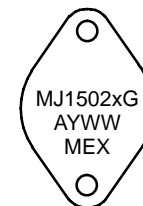
ON Semiconductor®

**16 AMPERES  
SILICON POWER TRANSISTORS  
200 – 250 VOLTS, 250 WATTS**



TO-204AA (TO-3)  
CASE 1-07  
STYLE 1

### MARKING DIAGRAM



MJ1502x = Device Code  
x = 2 or 4  
G = Pb-Free Package  
A = Assembly Location  
Y = Year  
WW = Work Week  
MEX = Country of Origin

### ORDERING INFORMATION

Device	Package	Shipping
MJ15022	TO-204	100 Units / Tray
MJ15022G	TO-204 (Pb-Free)	100 Units / Tray
MJ15024	TO-204	100 Units / Tray
MJ15024G	TO-204 (Pb-Free)	100 Units / Tray

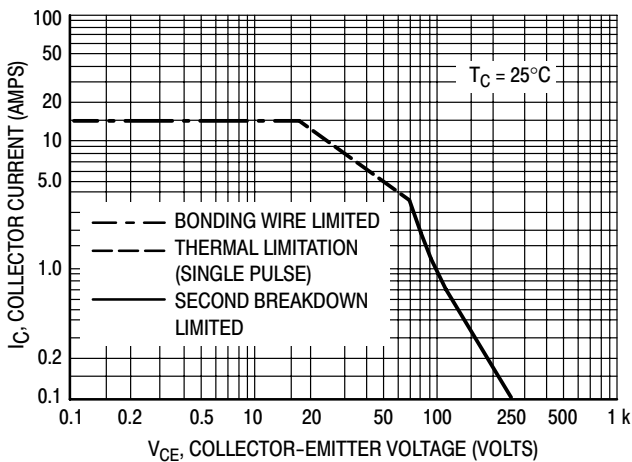
Preferred devices are recommended choices for future use and best overall value.

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## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage (Note 2) (I <sub>C</sub> = 100 mA <sub>dc</sub> , I <sub>B</sub> = 0)	MJ15022 MJ15024	V <sub>CEO(sus)</sub>	200 250	– –
Collector Cutoff Current (V <sub>CE</sub> = 200 V <sub>dc</sub> , V <sub>BE(off)</sub> = 1.5 V <sub>dc</sub> ) (V <sub>CE</sub> = 250 V <sub>dc</sub> , V <sub>BE(off)</sub> = 1.5 V <sub>dc</sub> )	MJ15022 MJ15024	I <sub>CEX</sub>	– –	250 250 μA <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 150 V <sub>dc</sub> , I <sub>B</sub> = 0) (V <sub>CE</sub> = 200 V <sub>dc</sub> , I <sub>B</sub> = 0)	MJ15022 MJ15024	I <sub>CEO</sub>	– –	500 500 μA <sub>dc</sub>
Emitter Cutoff Current (V <sub>CE</sub> = 5 V <sub>dc</sub> , I <sub>B</sub> = 0)		I <sub>EBO</sub>	–	500 μA <sub>dc</sub>
<b>SECOND BREAKDOWN</b>				
Second Breakdown Collector Current with Base Forward Biased (V <sub>CE</sub> = 50 V <sub>dc</sub> , t = 0.5 s (non–repetitive)) (V <sub>CE</sub> = 80 V <sub>dc</sub> , t = 0.5 s (non–repetitive))		I <sub>S/b</sub>	5 2	– – A <sub>dc</sub>
<b>ON CHARACTERISTICS</b>				
DC Current Gain (I <sub>C</sub> = 8 A <sub>dc</sub> , V <sub>CE</sub> = 4 V <sub>dc</sub> ) (I <sub>C</sub> = 16 A <sub>dc</sub> , V <sub>CE</sub> = 4 V <sub>dc</sub> )		h <sub>FE</sub>	15 5	60 –
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 8 A <sub>dc</sub> , I <sub>B</sub> = 0.8 A <sub>dc</sub> ) (I <sub>C</sub> = 16 A <sub>dc</sub> , I <sub>B</sub> = 3.2 A <sub>dc</sub> )		V <sub>CE(sat)</sub>	– –	1.4 4.0 V <sub>dc</sub>
Base–Emitter On Voltage (I <sub>C</sub> = 8 A <sub>dc</sub> , V <sub>CE</sub> = 4 V <sub>dc</sub> )		V <sub>BE(on)</sub>	–	2.2 V <sub>dc</sub>
<b>DYNAMIC CHARACTERISTICS</b>				
Current–Gain – Bandwidth Product (I <sub>C</sub> = 1 A <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f <sub>test</sub> = 1 MHz)		f <sub>T</sub>	4	– MHz
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)		C <sub>ob</sub>	–	500 pF

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.



**Figure 1. Active–Region Safe Operating Area**

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I<sub>C</sub> – V<sub>CE</sub> limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on T<sub>J(pk)</sub> = 200°C; T<sub>C</sub> is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values I<sub>on</sub> than the limitations imposed by second breakdown.

